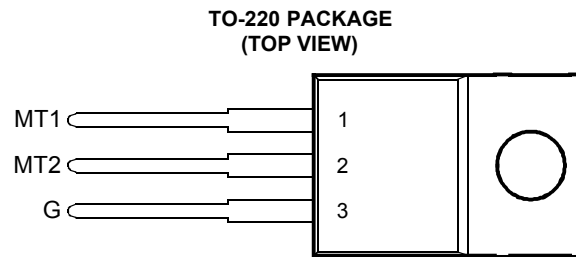


- Sensitive Gate Triacs
- 4 A RMS
- Glass Passivated Wafer
- 400 V to 700 V Off-State Voltage
- Max  $I_{GT}$  of 5 mA (Quadrants 1 - 3)



Pin 2 is in electrical contact with the mounting base.

MDC2ACA

### absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (see Note 1)	TIC206D	$V_{DRM}$	400	V
	TIC206M		600	
	TIC206S		700	
Full-cycle RMS on-state current at (or below) 85°C case temperature (see Note 2)		$I_{T(RMS)}$	4	A
Peak on-state surge current full-sine-wave at (or below) 25°C case temperature (see Note 3)		$I_{TSM}$	25	A
Peak gate current		$I_{GM}$	±0.2	A
Peak gate power dissipation at (or below) 85°C case temperature (pulse width ≤ 200 μs)		$P_{GM}$	1.3	W
Average gate power dissipation at (or below) 85°C case temperature (see Note 4)		$P_{G(AV)}$	0.3	W
Operating case temperature range		$T_C$	-40 to +110	°C
Storage temperature range		$T_{stg}$	-40 to +125	°C
Lead temperature 1.6 mm from case for 10 seconds		$T_L$	230	°C

- NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.  
 2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 85°C derate linearly to 110°C case temperature at the rate of 160 mA/°C.  
 3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.  
 4. This value applies for a maximum averaging time of 20 ms.

### electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$I_{DRM}$ Repetitive peak off-state current	$V_D = \text{rated } V_{DRM}$	$I_G = 0$	$T_C = 110^\circ\text{C}$			±1	mA
$I_{GT}$ Gate trigger current	$V_{supply} = +12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		0.9	5	mA
	$V_{supply} = +12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-2.2	-5	
	$V_{supply} = -12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-1.8	-5	
	$V_{supply} = -12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		2.4	10	
$V_{GT}$ Gate trigger voltage	$V_{supply} = +12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		0.7	2	V
	$V_{supply} = +12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-0.7	-2	
	$V_{supply} = -12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-0.7	-2	
	$V_{supply} = -12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		0.7	2	

† All voltages are with respect to Main Terminal 1.

## PRODUCT INFORMATION

Information is current as of publication date. Products conform to specifications in accordance with the terms of Power Innovations standard warranty. Production processing does not necessarily include testing of all parameters.

# TIC206 SERIES SILICON TRIACS

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## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_T$ On-state voltage	$I_T = \pm 4.2$ A	$I_G = 50$ mA	(see Note 5)		$\pm 1.4$	$\pm 2.2$	V
$I_H$ Holding current	$V_{supply} = +12$ V† $V_{supply} = -12$ V†	$I_G = 0$	Init' $I_{TM} = 100$ mA Init' $I_{TM} = -100$ mA		1.5 -1.3	15 -15	mA
$I_L$ Latching current	$V_{supply} = +12$ V† $V_{supply} = -12$ V†	(see Note 6)				30 -30	mA
dv/dt Critical rate of rise of off-state voltage	$V_{DRM} = \text{Rated } V_{DRM}$	$I_G = 0$	$T_C = 110^\circ\text{C}$		$\pm 20$		V/ $\mu$ s
dv/dt <sub>(c)</sub> Critical rise of commutation voltage	$V_{DRM} = \text{Rated } V_{DRM}$	$I_{TRM} = \pm 4.2$ A	$T_C = 85^\circ\text{C}$	$\pm 1$	$\pm 3$		V/ $\mu$ s

† All voltages are with respect to Main Terminal 1.

NOTES: 5. This parameter must be measured using pulse techniques,  $t_p \leq 1$  ms, duty cycle  $\leq 2\%$ . Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

6. The triacs are triggered by a 15-V (open circuit amplitude) pulse supplied by a generator with the following characteristics:  
 $R_G = 100 \Omega$ ,  $t_{p(g)} = 20 \mu\text{s}$ ,  $t_r \leq 15$  ns,  $f = 1$  kHz.

## thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			7.8	$^\circ\text{C/W}$
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	$^\circ\text{C/W}$

## TYPICAL CHARACTERISTICS

GATE TRIGGER CURRENT  
VS  
TEMPERATURE

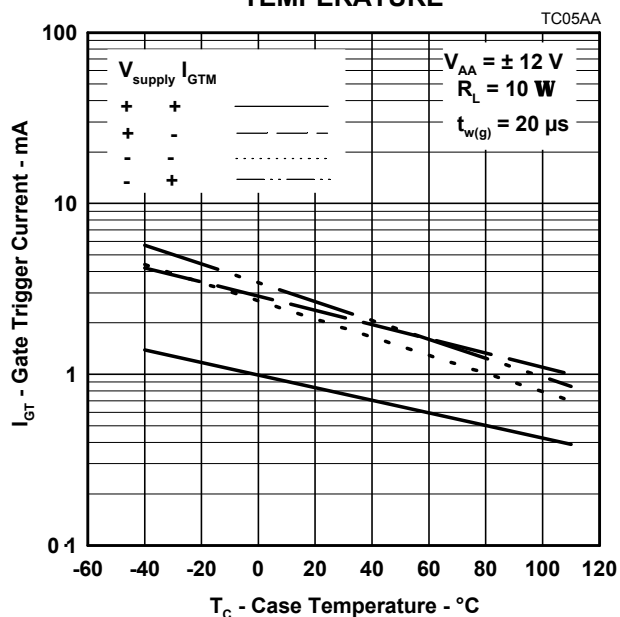


Figure 1.

GATE TRIGGER VOLTAGE  
VS  
TEMPERATURE

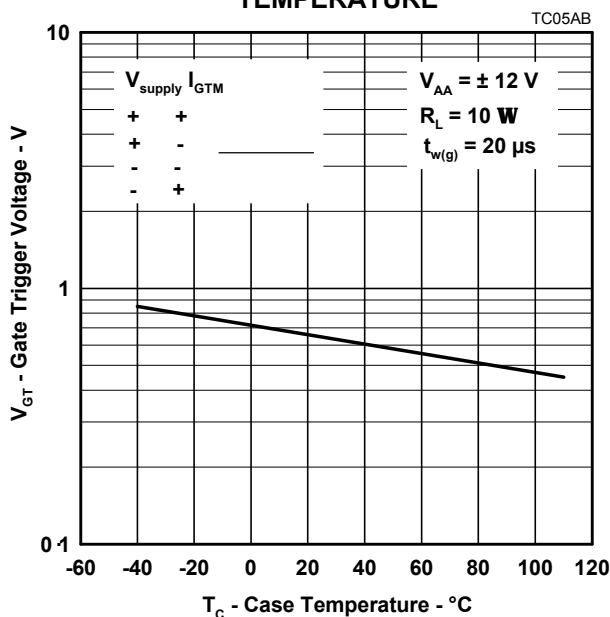


Figure 2.

## PRODUCT INFORMATION

TYPICAL CHARACTERISTICS

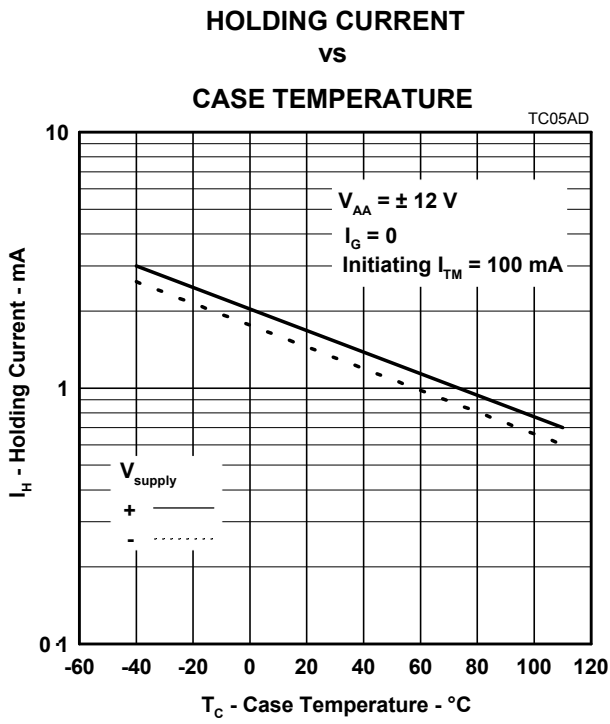


Figure 3.

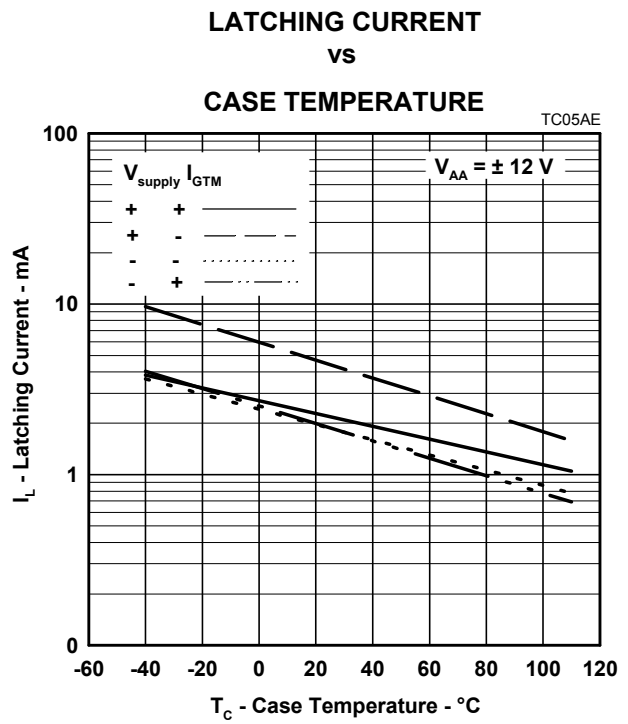


Figure 4.

# TIC206 SERIES SILICON TRIACS

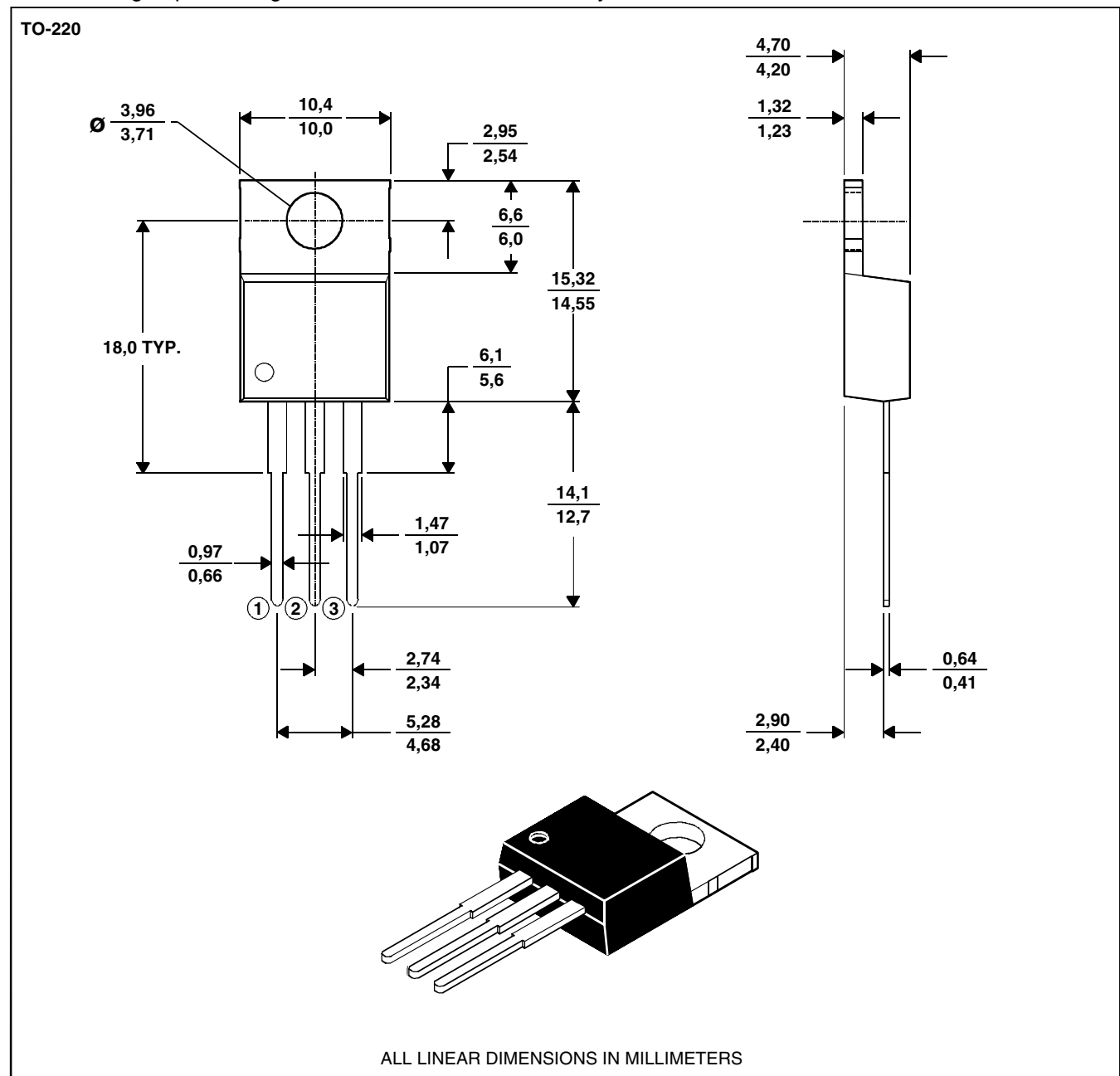
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## MECHANICAL DATA

### TO-220

#### 3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTE A: The centre pin is in electrical contact with the mounting tab.

## PRODUCT INFORMATION

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